

Thermally-Enhanced High Power RF LDMOS FETs 240 W, 1805 – 1880 MHz

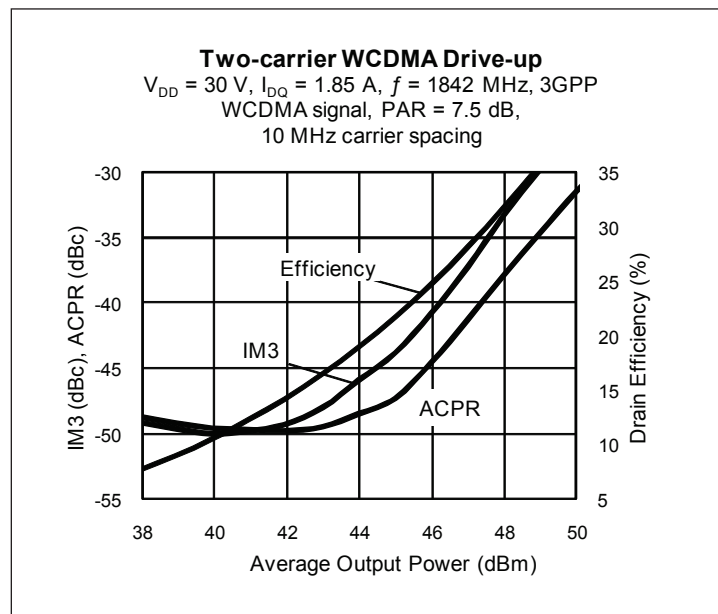
Description

The PTFB182503EL and PTFB182503FL are 240-watt LDMOS FETs intended for use in multi-standard cellular power amplifier applications in the 1805 to 1880 MHz frequency band. Features include input and output matching, high gain, wide signal bandwidth and reduced memory effects for improved DPD correctability. Manufactured with Infineon's advanced LDMOS process, these devices provide excellent thermal performance and superior reliability.

PTFB182503EL
H-33288-6



PTFB182503FL
H-34288-4/2



Features

- Broadband internal input and output matching
- Enhanced for use in DPD error correction systems
- Typical two-carrier WCDMA performance, 1880 MHz, 30 V
 - Average output power = 50 W
 - Linear gain = 19 dB
 - Drain efficiency = 28 %
 - Intermodulation distortion = -35 dBc
- Typical CW performance, 1880 MHz, 30 V
 - Output power at P_{1dB} = 240 W
 - Efficiency = 55%
- Increased negative gate-source voltage range for improved performance in Doherty peaking amplifiers
- Integrated ESD protection. Human Body Model, Class 2 (minimum)
- Capable of handling 10:1 VSWR @ 30 V, 240 W (CW) output power
- Pb-free, RoHS-compliant

RF Characteristics

Two-carrier WCDMA Specifications (tested in Infineon test fixture)

$V_{DD} = 30\text{ V}$, $I_{DQ} = 1.85\text{ A}$, $P_{OUT} = 50\text{ W}$ average

$f_1 = 1840\text{ MHz}$, $f_2 = 1845\text{ MHz}$, 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 7.5 dB @ 0.01% CCDF

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	18	19	—	dB
Drain Efficiency	η_D	27	28	—	%
Intermodulation Distortion	IMD	—	-35	-31	dBc

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

RF Characteristics (cont.)

Two-tone Specifications (not subject to production test—verified by design/characterization in Infineon test fixture)
 $V_{DD} = 30\text{ V}$, $I_{DQ} = 1.85\text{ A}$, $P_{OUT} = 220\text{ W PEP}$, $f = 1840\text{ MHz}$, tone spacing = 1 MHz

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	—	18	—	dB
Drain Efficiency	η_D	—	40	—	%
Intermodulation Distortion	IMD	—	−28	—	dBc

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1.0	μA
Drain Leakage Current	$V_{DS} = 63\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10.0	μA
On-State Resistance	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.03	—	Ω
Operating Gate Voltage	$V_{DS} = 30\text{ V}$, $I_{DQ} = 1.85\text{ A}$	V_{GS}	2.3	2.8	3.3	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1.0	μA

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	65	V
Gate-Source Voltage	V_{GS}	−6 to +10	V
Junction Temperature	T_J	200	°C
Storage Temperature Range	T_{STG}	−40 to +150	°C
Thermal Resistance ($T_{CASE} = 70^\circ\text{C}$, 50 W WCDMA)	$R_{\theta JC}$	0.262	°C/W

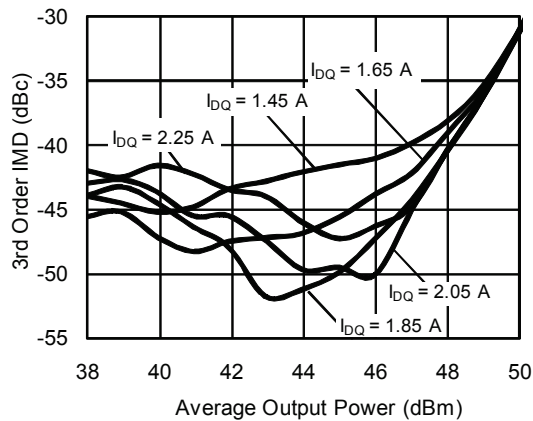
Ordering Information

Type and Version	Package Outline	Package Description	Shipping
PTFB182503EL V1	H-33288-6	Thermally-enhanced slotted flange, single-ended	Tray
PTFB182503EL V1 R250	H-33288-6	Thermally-enhanced slotted flange, single-ended	Tape & Reel, 250 pcs
PTFB182503FL V2	H-34288-4/2	Thermally-enhanced earless flange, single-ended	Tray
PTFB182503FL V2 R250	H-34288-4/2	Thermally-enhanced earless flange, single-ended	Tape & Reel, 250 pcs

Typical Performance (data taken in a production test fixture)

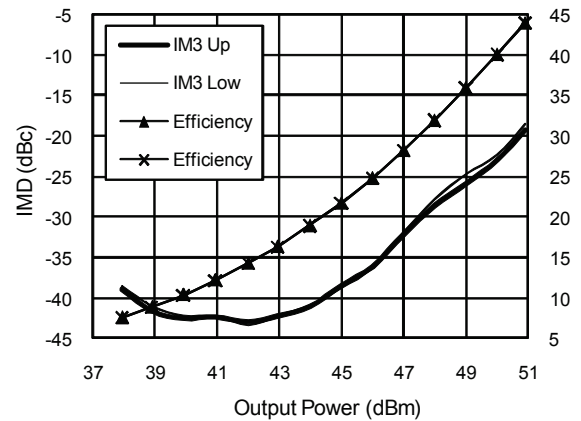
Two-Carrier WCDMA at Various Biases

$V_{DD} = 30\text{ V}$, $f = 1842\text{ MHz}$, 3GPP WCDMA signal, PAR = 7.5 dB, 5 MHz carrier spacing



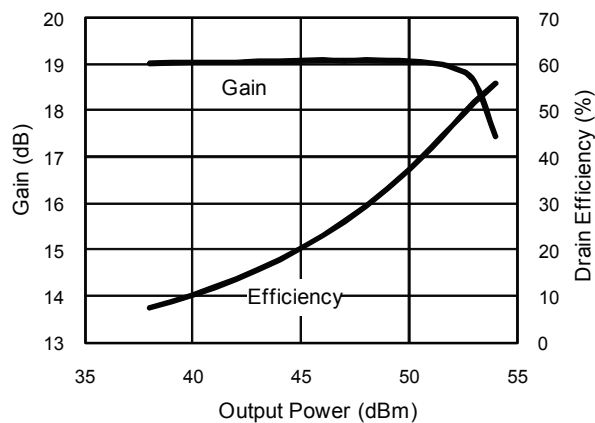
Six-Carrier GSM vs Power Out

$V_{DD} = 30\text{ V}$, $I_{DQ} = 1.85\text{ A}$, $f = 1842\text{ MHz}$, PAR = 7.1 dB



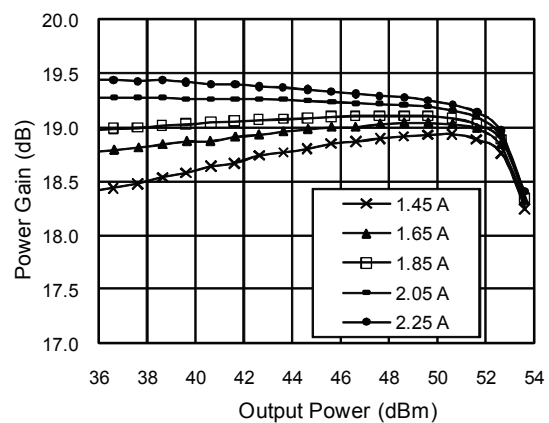
CW Performance Gain & Efficiency vs. Output Power

$V_{DD} = 30\text{ V}$, $I_{DQ} = 1.85\text{ A}$, $f = 1842\text{ MHz}$

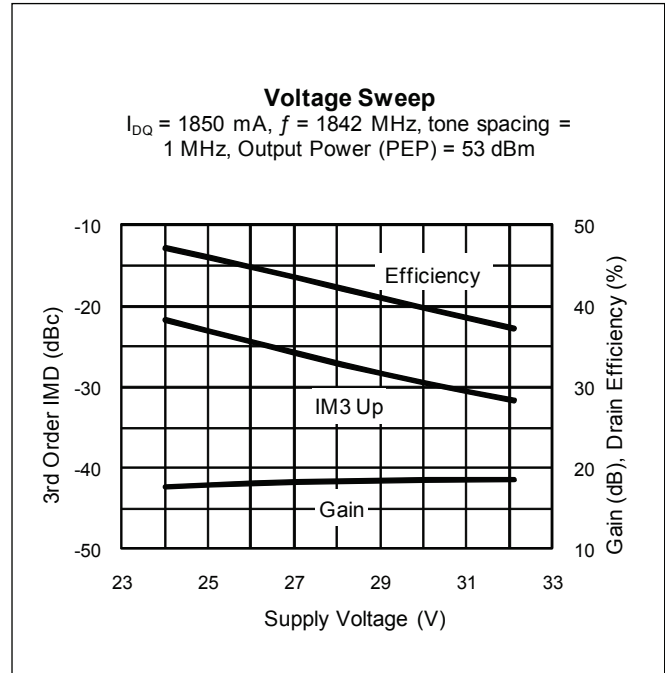
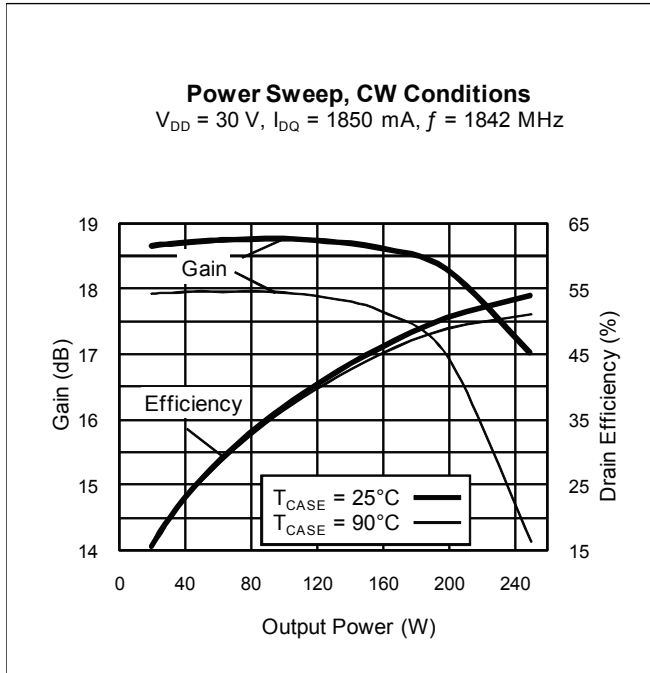


Power Sweep

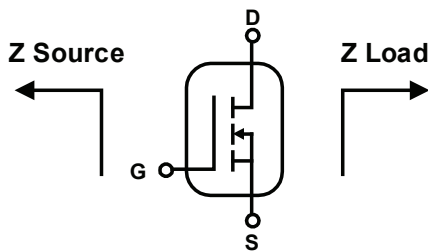
$V_{DD} = 30\text{ V}$, $f = 1842\text{ MHz}$



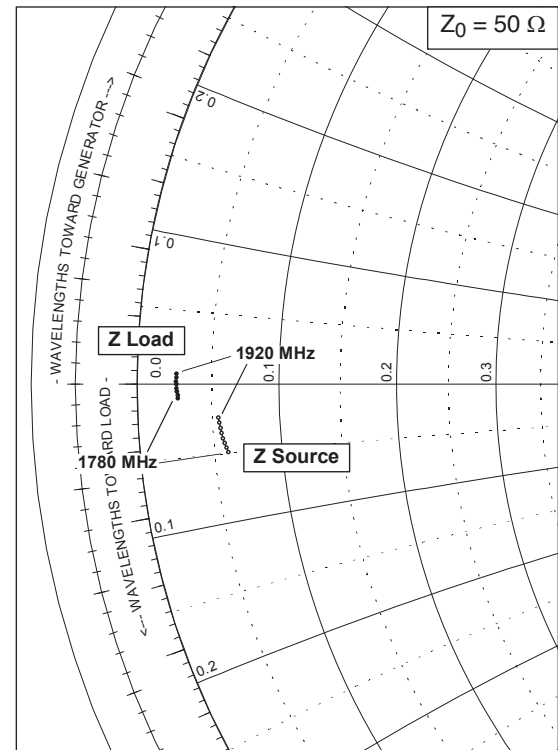
Typical Performance (cont.)



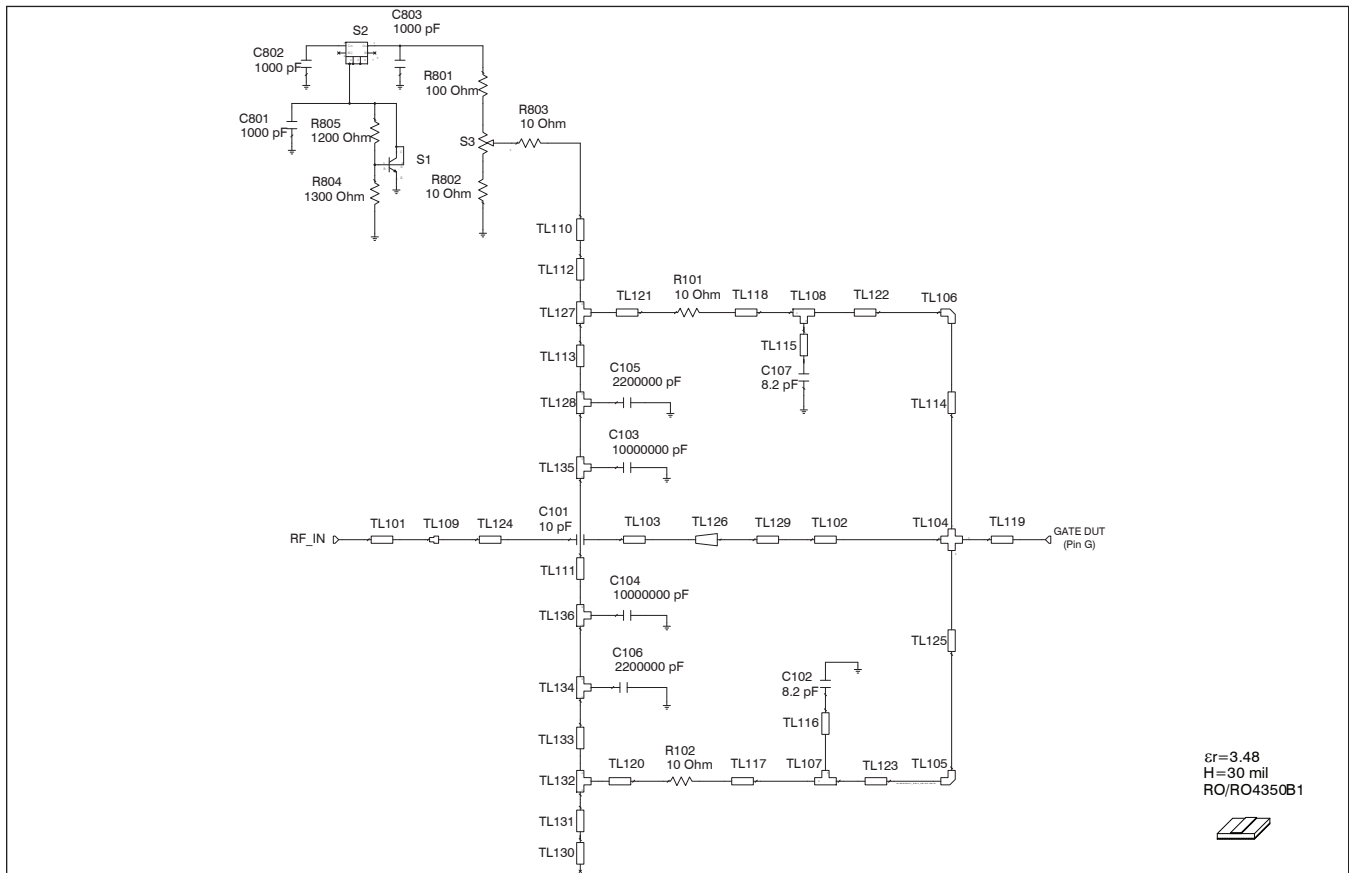
Broadband Circuit Impedance



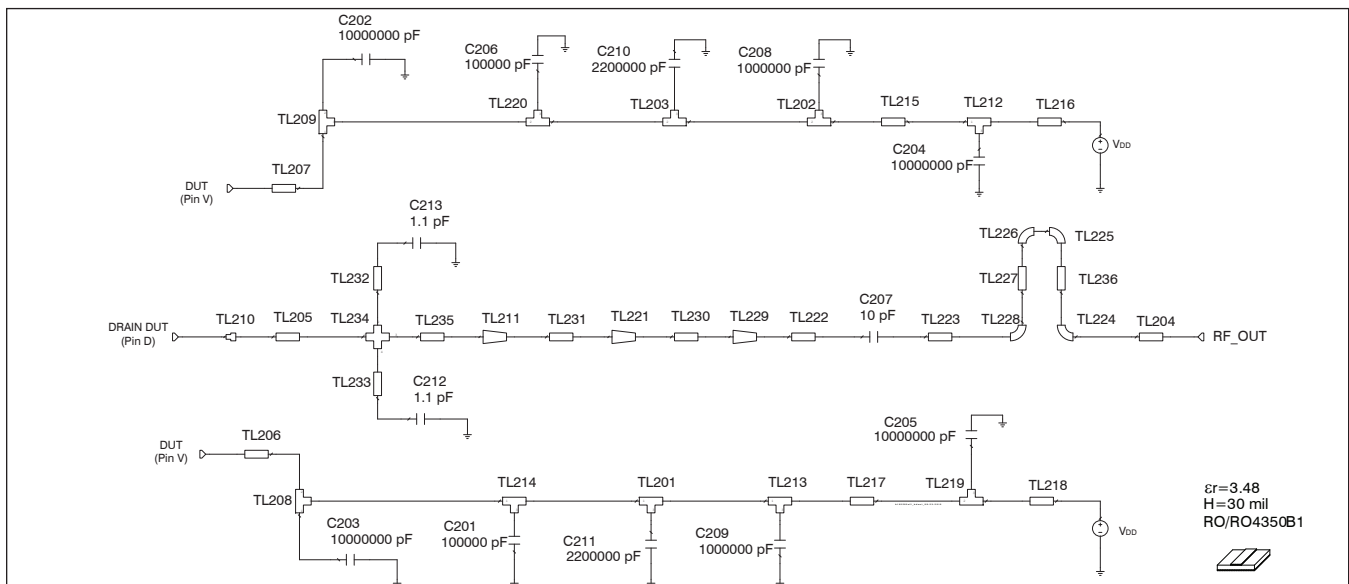
Frequency	Z Source Ω		Z Load Ω	
MHz	R	jX	R	jX
1780	2.99	-2.48	1.33	-0.49
1800	2.95	-2.30	1.33	-0.38
1820	2.89	-2.13	1.31	-0.27
1840	2.84	-1.96	1.29	-0.16
1860	2.80	-1.76	1.29	-0.02
1880	2.78	-1.58	1.28	0.10
1900	2.74	-1.39	1.29	0.23
1920	2.72	-1.21	1.29	0.36



Reference Circuit



Reference circuit input schematic for $f = 1880$ MHz



Reference circuit output schematic for $f = 1880$ MHz

Reference Circuit (cont.)

Description

DUT	PTFB182503EL or PTFB182503FL
PCB	0.76 mm [.030"] thick, $\epsilon_r = 3.48$, Rogers 4350, 1 oz. copper

Electrical Characteristics at 1880 MHz

Transmission Line	Electrical Characteristics	Dimensions: mm	Dimensions: mils
Input			
TL101, TL117	0.022λ , 78.27 Ω	$W = 0.762$, $L = 2.159$	$W = 30$, $L = 85$
TL102	0.035λ , 51.58 Ω	$W = 1.651$, $L = 3.358$	$W = 65$, $L = 132$
TL103	0.050λ , 9.67 Ω	$W = 13.970$, $L = 4.445$	$W = 550$, $L = 175$
TL104	0.031λ , 51.58 Ω	$W = 1.651$, $L = 3.018$	$W = 65$, $L = 119$
TL105		$W1 = 13.970$, $W2 = 0.762$, $W3 = 13.970$, $W4 = 0.762$	$W1 = 550$, $W2 = 30$, $W3 = 550$, $W4 = 30$
TL106, TL107		$W = 0.762$	$W = 30$
TL108, TL136	0.010λ , 68.02 Ω	$W1 = 1.016$, $W2 = 1.016$, $W3 = 1.016$	$W1 = 40$, $W2 = 40$, $W3 = 40$
TL109, TL110, TL132, TL139	0.010λ , 78.27 Ω	$W1 = 0.762$, $W2 = 0.762$, $W3 = 1.016$	$W1 = 30$, $W2 = 30$, $W3 = 40$
TL111		$W1 = 1.651$, $W2 = 2.032$	$W1 = 65$, $W2 = 80$
TL112, TL134	0.014λ , 38.82 Ω	$W = 2.540$, $L = 1.321$	$W = 100$, $L = 52$
TL113	0.020λ , 78.27 Ω	$W = 0.762$, $L = 2.007$	$W = 30$, $L = 79$
TL114	0.099λ , 92.53 Ω	$W = 0.508$, $L = 9.957$	$W = 20$, $L = 392$
TL115	0.016λ , 68.02 Ω	$W = 1.016$, $L = 1.524$	$W = 40$, $L = 60$
TL116, TL137	0.017λ , 78.27 Ω	$W = 0.762$, $L = 1.727$	$W = 30$, $L = 68$
TL118, TL119	0.001λ , 68.02 Ω	$W = 1.016$, $L = 0.127$	$W = 40$, $L = 5$
TL120, TL121	0.013λ , 78.27 Ω	$W = 0.762$, $L = 1.270$	$W = 30$, $L = 50$
TL122	0.022λ , 9.67 Ω	$W = 13.970$, $L = 1.981$	$W = 550$, $L = 78$
TL123, TL124	0.007λ , 68.02 Ω	$W = 1.016$, $L = 0.686$	$W = 40$, $L = 27$
TL125, TL126	0.118λ , 78.27 Ω	$W = 0.762$, $L = 11.684$	$W = 30$, $L = 460$
TL127	0.008λ , 45.17 Ω	$W = 2.032$, $L = 0.762$	$W = 80$, $L = 30$
TL128	0.000λ , 45.17 Ω	$W = 2.032$, $L = 0.025$	$W = 80$, $L = 1$
TL129	0.023λ , 9.67 Ω	$W1 = 13.970$, $W2 = 13.970$, $W3 = 2.032$	$W1 = 550$, $W2 = 550$, $W3 = 80$
TL130	0.000λ , 9.67 Ω	$W = 13.970$, $L = 0.025$	$W = 550$, $L = 1$
TL131 (taper)	0.028λ , 9.67 Ω / 51.58 Ω	$W1 = 13.970$, $W2 = 1.651$, $L = 2.515$	$W1 = 550$, $W2 = 65$, $L = 99$
TL133	0.050λ , 9.67 Ω	$W = 13.970$, $L = 4.470$	$W = 550$, $L = 176$
TL135	0.015λ , 68.02 Ω	$W = 1.016$, $L = 1.514$	$W = 40$, $L = 60$
TL138	0.010λ , 78.27 Ω	$W = 0.762$, $L = 0.991$	$W = 30$, $L = 39$

table continued on page 7

Reference Circuit (cont.)

Electrical Characteristics at 1880 MHz

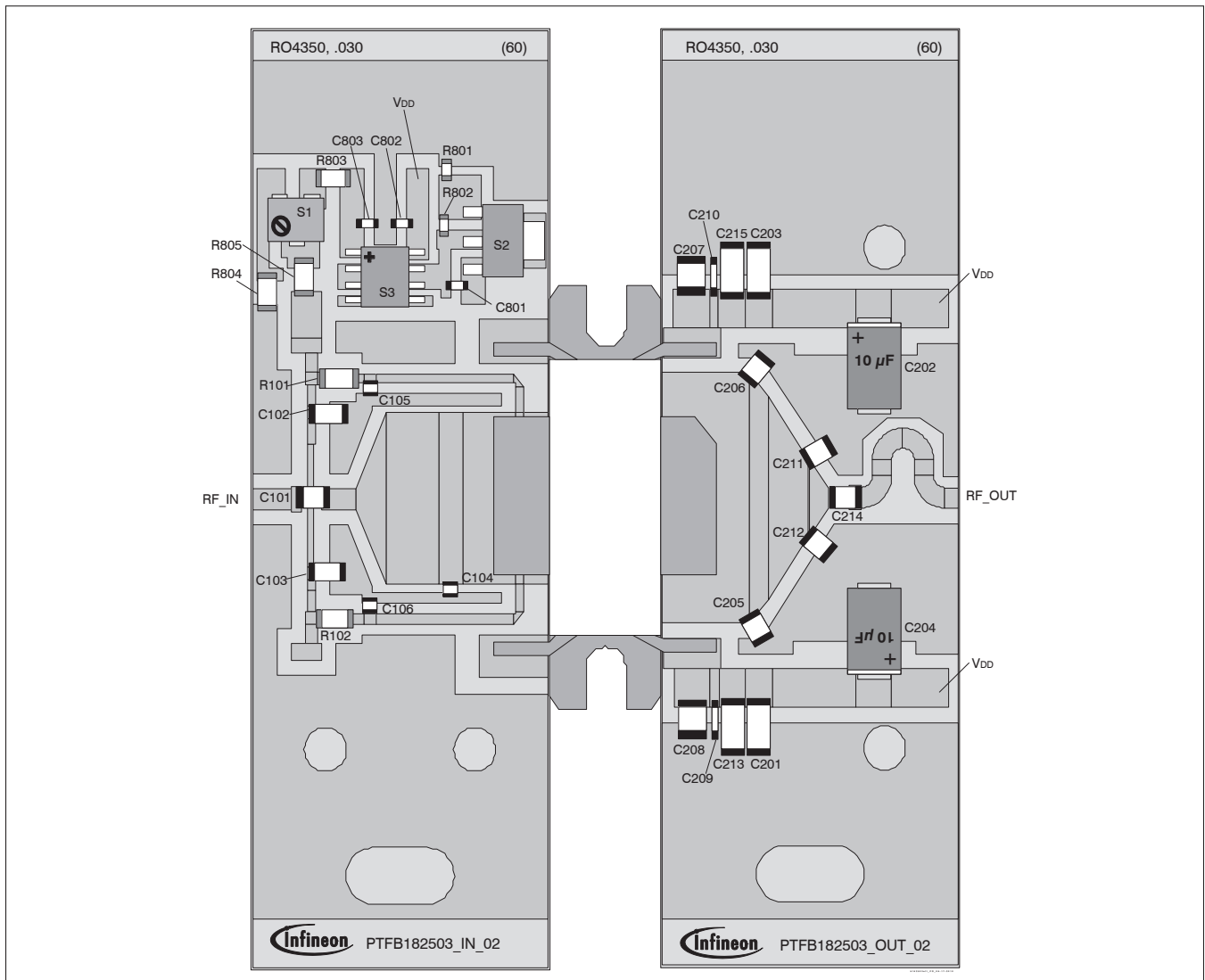
Transmission Line	Electrical Characteristics	Dimensions: mm	Dimensions: mils
Output			
TL201, TL219, TL220, TL222		W = 0.002, ANG = 90.000, R = 0.002	W = 2, ANG = 3543307, R = 70
TL202		W1 = 1.651, W2 = 2.032	W1 = 65, W2 = 80
TL203	0.012 λ , 51.58 Ω	W = 1.651, L = 1.118	W = 65, L = 44
TL204	0.084 λ , 6.86 Ω	W = 20.320, L = 7.366	W = 800, L = 290
TL205	0.011 λ , 45.17 Ω	W = 2.032, L = 1.016	W = 80, L = 40
TL206	0.028 λ , 23.60 Ω	W = 4.928, L = 2.540	W = 194, L = 100
TL207	0.028 λ , 23.79 Ω	W = 4.877, L = 2.540	W = 192, L = 100
TL208 (taper)	0.018 λ , 6.86 Ω / 8.31 Ω	W1 = 20.320, W2 = 16.510, L = 1.575	W1 = 800, W2 = 650, L = 62
TL209, TL210	0.076 λ , 34.08 Ω	W = 3.048, L = 7.112	W = 120, L = 280
TL211, TL216, TL224, TL225	0.032 λ , 34.08 Ω	W1 = 3.048, W2 = 3.048, W3 = 3.048	W1 = 120, W2 = 120, W3 = 120
TL212, TL228, TL217, TL218, TL227	0.024 λ , 34.08 Ω	W1 = 3.048, W2 = 3.048, W3 = 2.286	W1 = 120, W2 = 120, W3 = 90
TL213	0.008 λ , 34.08 Ω	W1 = 3.048, W2 = 3.048, W3 = 0.762	W1 = 120, W2 = 120, W3 = 30
TL214, TL215	0.051 λ , 34.08 Ω	W = 3.048, L = 4.826	W = 120, L = 190
TL221, TL242	0.013 λ , 51.58 Ω	W = 1.651, L = 1.270	W = 65, L = 50
TL223 (taper)	0.018 λ , 19.45 Ω / 51.58 Ω	W1 = 6.248, W2 = 1.651, L = 1.651	W1 = 246, W2 = 65, L = 65
TL226		W1 = 12.700, W2 = 17.780	W1 = 500, W2 = 700
TL229, TL230	0.000 λ , 19.45 Ω	W = 6.248, L = 0.025	W = 246, L = 1
TL231 (taper)	0.038 λ , 8.31 Ω / 19.45 Ω	W1 = 16.510, W2 = 6.248, L = 3.378	W1 = 650, W2 = 246, L = 133
TL232		W1 = 6.248, W2 = 0.025, W3 = 6.248, W4 = 0.025	W1 = 246, W2 = 1, W3 = 246, W4 = 1
TL233, TL234, TL237, TL238	0.000 λ , 146.88 Ω	W = 0.025, L = 0.025	W = 1, L = 1
TL235	0.005 λ , 51.58 Ω	W = 1.651, L = 0.508	W = 65, L = 20
TL236	0.000 λ , 8.31 Ω	W = 16.510, L = 0.025	W = 650, L = 1
TL239		W1 = 20.320, W2 = 0.025, W3 = 20.320, W4 = 0.025	W1 = 800, W2 = 1, W3 = 800, W4 = 1
TL240, TL241	0.000 λ , 6.86 Ω	W = 20.320, L = 0.025	W = 800, L = 1

Reference Circuit (cont.)

Circuit Assembly Information

Test Fixture Part No. LTN/PTFB182503EF

Find Gerber files for this test fixture on the Infineon Web site at <http://www.infineon.com/rfpower>



Reference circuit assembly diagram (not to scale)

Reference Circuit (cont.)

Component	Description	Suggested Manufacturer	P/N
Input			
C101	Chip capacitor, 7.5 pF	ATC	ATC100B7R5BW500XB
C102, C103	Chip capacitor, 4.71 μ F	ATC	493-2372-2-ND
C104	Chip capacitor, 0.3 pF	ATC	ATC100A0R3BW150XB
C105, C106	Chip capacitor, 10 pF	ATC	ATC100A100FW150XB
C801, C802, C803	Capacitor, 1000 pF	Digi-Key	PCC1772CT-ND
R101, R102, R804, R805	Resistor, 10 Ω	Digi-Key	P10ECT-ND
R801	Resistor, 1300 Ω	Digi-Key	P1.3KGCT-ND
R802	Resistor, 1200 Ω	Digi-Key	P1.2KGCT-ND
R803	Resistor, 100 Ω	Digi-Key	P100ECT-ND
S1	Potentiometer, 2k Ω	Digi-Key	3224W-202ECT-ND
S2	Transistor	Digi-Key	BCP5616TA-ND
S3	Voltage Regulator	Digi-Key	LM78L05ACM-ND
Output			
C201, C203	Chip capacitor, 0.1 μ F	Digi-Key	445-1411-2-ND
C202, C204	Capacitor, 10 μ F	Garrett Electronics	281M5002106K
C205, C206	Chip capacitor, 0.6 pF	ATC	ATC100B0R6BW500XB
C207, C208	Chip capacitor, 10 μ F	Digi-Key	587-1818-2-ND
C209, C210	Chip capacitor, 0.1 μ F	Digi-Key	399-1267-2-ND
C211, C212	Chip capacitor, 0.9 pF	ATC	ATC100B0R9BW500XB
C213, C215	Chip capacitor, 2.2 μ F	Digi-Key	445-1447-2-ND
C214	Chip capacitor, 10 pF	ATC	ATC100B100FW500XB

Package Outline Specifications

Package H-33288-6

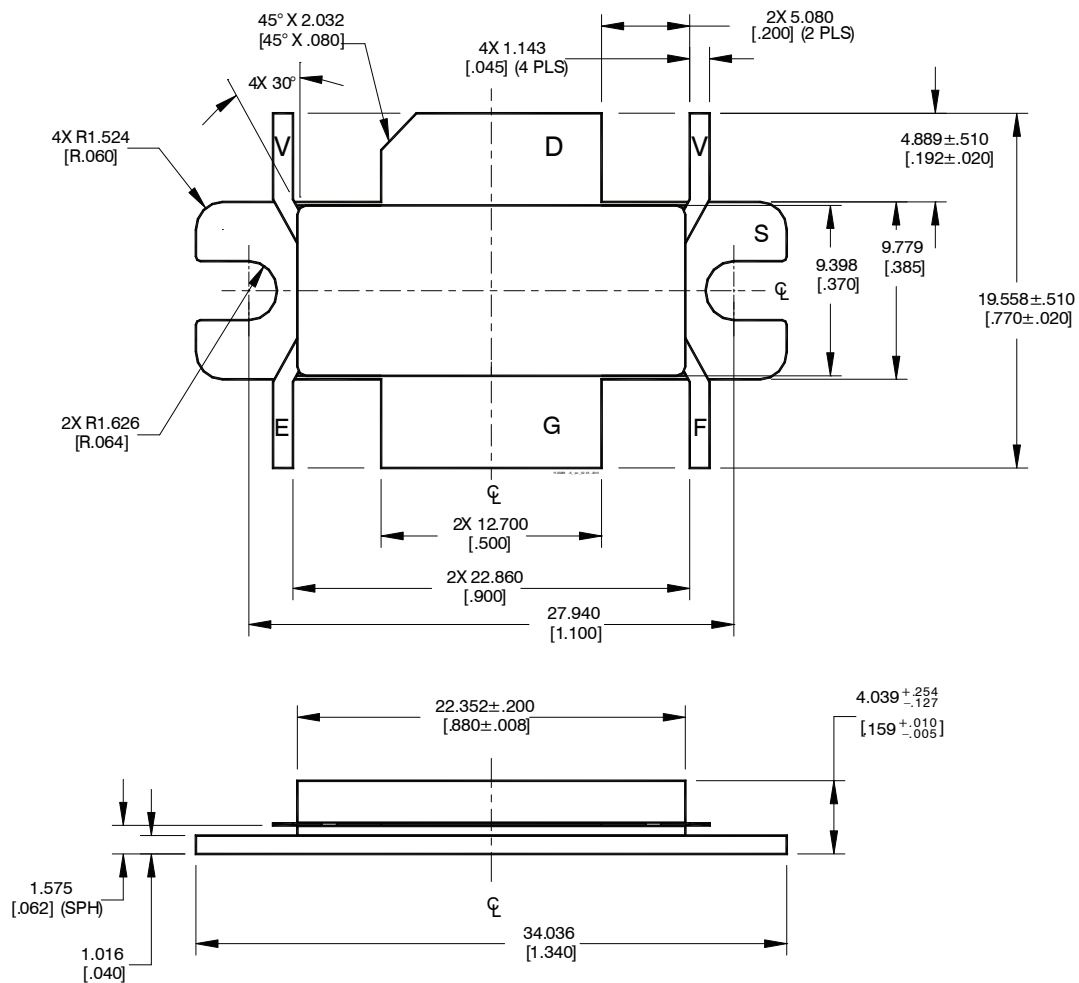


Diagram Notes—unless otherwise specified:

1. Interpret dimensions and tolerances per ASME Y14.5M-1994.
2. Primary dimensions are mm. Alternate dimensions are inches.
3. All tolerances ± 0.127 [.005] unless specified otherwise.
4. Pins: G = gate, S = source, D = drain, V = V_{DD} , E, F = N.C.
5. Lead thickness: 0.10 + 0.051/−0.025 mm [.004 +0.002/−0.001 inch].
6. Gold plating thickness: 0.25 micron [10 microinch] max.

Package Outline Specifications (cont.)

Package H-34288-4/2

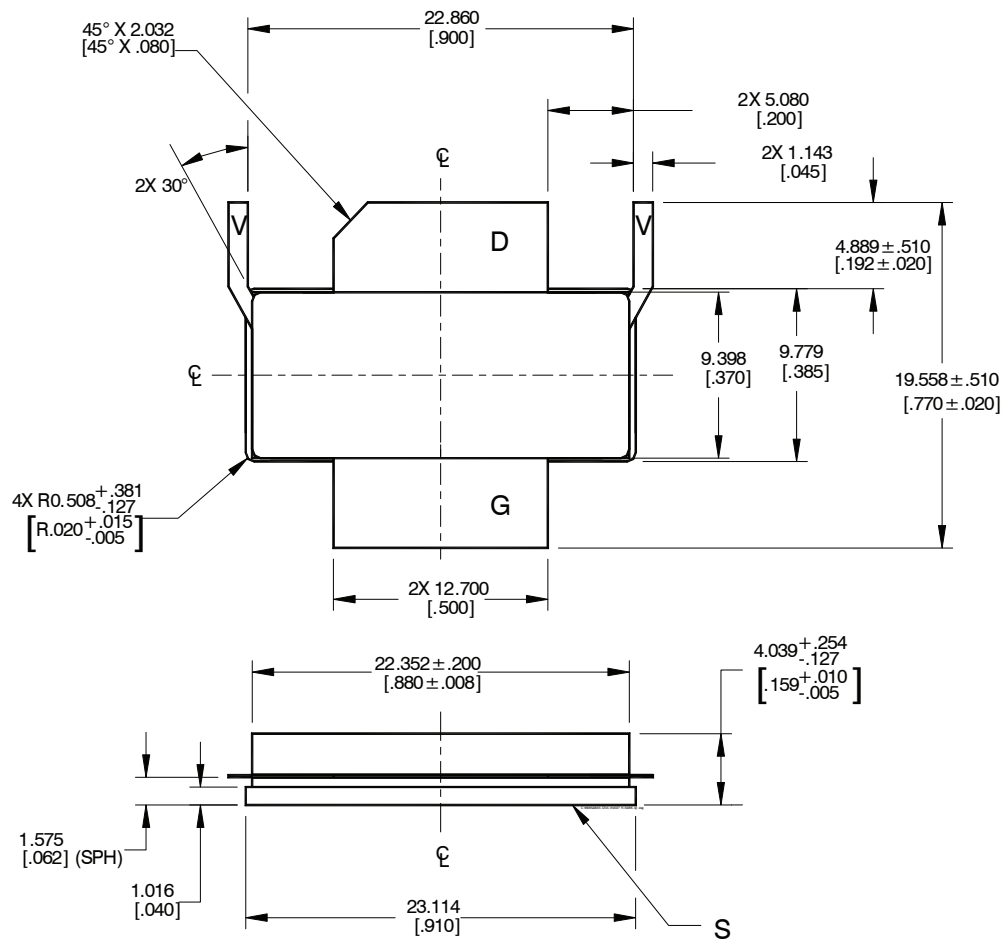


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<http://www.infineon.com/rfpower>

Revision History: 2010-11-09

Data Sheet

Previous Version: 2010-10-07, Data Sheet

Page	Subjects (major changes since last revision)
1, 2, 10	Changed eared flange package type
1	Updated VSWR specification to 10:1

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